NSN 5961-01-058-6626



Transistor - Page 1 of 1 View Online at https://aerobasegroup.com/nsn/5961-01-058-6626 **Inclosure Material:** Metal **Overall Length:** Between 0.120 inches and 0.140 inches Overall Diameter: 0.300 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact-darlington connected **Electrode Internally-electrically Connected To Case:** Emitter **Mounting Method:** Threaded stud **Thread Size:** 0.164 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 33.0 collector to emitter voltage/static/base open and 60.0 collector to emitter voltage, dc with base short-circuited to emitter and 4.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 250.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 2.1 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Test Data Document:** 99971-7536771 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Thread Series Designator:** Unc **Terminal Type And Quantity:** 2 ribbon and 1 threaded stud Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: